

# Bus Buffer with 3-State Output NL17SG125

The NL17SG125 MiniGate<sup>™</sup> is an advanced high-speed CMOS Bus Buffer with 3-State Output in ultra-small footprint.

The NL17SG125 input structures provides protection when voltages up to 3.6 V are applied.

#### **Features**

- Wide Operating V<sub>CC</sub> Range: 0.9 V to 3.6 V
- High Speed:  $t_{PD} = 2.4 \text{ ns}$  (Typ) at  $V_{CC} = 3.0 \text{ V}$ ,  $C_L = 15 \text{ pF}$
- Low Power Dissipation:  $I_{CC} = 0.5 \mu A$  (Max) at  $T_A = 25^{\circ}C$
- 3.6 V Overvoltage Tolerant (OVT) Input Pins
- I<sub>OFF</sub> Supports Partial Power Down Protection
- Ultra-Small Packages
- –Q Suffix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant

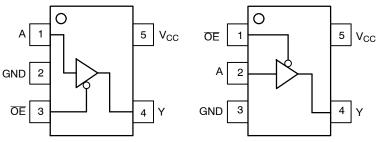


Figure 1. SOT-953 (Top Thru View)

Figure 2. SC-88A (Top View)

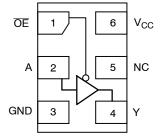






Figure 4. Logic Symbol

#### **PIN ASSIGNMENT**

Pin Number	SOT-953	SC-88A	UDFN6
1	Α	ŌĒ	ŌĒ
2	GND	Α	Α
3	ŌĒ	GND	GND
4	Υ	Υ	Υ
5	V <sub>CC</sub>	V <sub>CC</sub>	NC
6			V <sub>CC</sub>

### MARKING DIAGRAMS



SC-88A DF SUFFIX CASE 419A





SOT-953 CASE 527AE





UDFN6 1.0 x 1.0 CASE 517BX





UDFN6 1.45 x 1.0 CASE 517AQ



XX = Specific Device Code

M = Date Code\*■ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or position may vary depending upon manufacturing location.

#### **FUNCTION TABLE**

A Input	OE Input	Y Output
L	L	L
н	L	Н
×	Н	Z

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

**Table 1. MAXIMUM RATINGS** 

Symbol	Paramet	Value	Unit	
V <sub>CC</sub>	DC Supply Voltage		-0.5 to +4.3	V
V <sub>IN</sub>	DC Input Voltage		-0.5 to +4.3	V
V <sub>OUT</sub>	DC Output Voltage	Active-Mode (High or Low State)  Tri-State Mode (Note 1)  Power-Down Mode (V <sub>CC</sub> = 0 V)	-0.5 to V <sub>CC</sub> + 0.5 -0.5 to +4.3 -0.5 to +4.3	V
I <sub>IK</sub>	DC Input Diode Current	V <sub>IN</sub> < GND	-20	mA
I <sub>OK</sub>	DC Output Diode Current	V <sub>OUT</sub> < GND	-20	mA
I <sub>OUT</sub>	DC Output Source/Sink Current	±20	mA	
I <sub>CC or</sub> I <sub>GND</sub>	DC Supply Current Per Supply Pin or Grour	nd Pin	±20	mA
T <sub>STG</sub>	Storage Temperature Range		-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10	260	°C	
TJ	Junction Temperature Under Bias		+150	°C
$\theta_{JA}$	Thermal Resistance (Note 2)	SC-88A SOT-953 UDFN6	377 254 154	°C/W
P <sub>D</sub>	Power Dissipation in Still Air at 85°C	SC-88A SOT-953 UDFN6	332 491 812	mW
MSL	Moisture Sensitivity		Level 1	
F <sub>R</sub>	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	
V <sub>ESD</sub>	ESD Withstand Voltage (Note 3)	Human Body Model Charged Device Model	2000 1000	V
I <sub>LATCHUP</sub>	Latchup Performance (Note 4)		±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Applicable to devices with outputs that may be tri-stated.
- Applicable to devices with outputs that may be the stated.
   Measured with minimum pad spacing on an FR4 board, using 10 mm by 1inch, 2 ounce copper trace no air flow per JESD51–7.
   HBM tested to EIA / JESD22–A114–A. CDM tested to JESD22–C101–A. JEDEC recommends that ESD qualification to EIA/JESD22–A115A (Machine Model) be discontinued.
  4. Tested to EIA/JESD78 Class II.

**Table 2. RECOMMENDED OPERATING CONDITIONS** 

Symbol	Parameter		Min	Max	Unit
V <sub>CC</sub>	Positive DC Supply Voltage		0.9	3.6	V
V <sub>IN</sub>	Digital Input Voltage		0	3.6	V
V <sub>OUT</sub>	Output Voltage	Active Mode (High or Low State)	0	V <sub>CC</sub>	V
		Tri-State Mode (Note 1)	0	3.6	
		Power Down Mode (V <sub>CC</sub> = 0 V)	0	3.6	
T <sub>A</sub>	Operating Free-Air Temperature		-55	+125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Transition Rise or Fall Rate	$V_{CC}$ = 3.3 V $\pm$ 0.3 V	0	10	nS/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

Table 3. DC ELECTRICAL CHARACTERISTICS

				7	T <sub>A</sub> = 25°C		T <sub>A</sub> = -55°C	to +125°C	
Symbol	Parameter	Conditions	V <sub>CC</sub> (V)	Min	Тур	Max	Min	Max	Unit
V <sub>IH</sub>	High-Level Input		0.9	-	$V_{CC}$	-	-	_	V
	Voltage		1.1 to 1.3	0.7 x V <sub>CC</sub>	-	-	0.7 x V <sub>CC</sub>	_	
			1.4 to 1.6	0.65 x V <sub>CC</sub>	-	-	0.65 x V <sub>CC</sub>	_	
			1.65 to 1.95	0.65 x V <sub>CC</sub>	-	-	0.65 x V <sub>CC</sub>	_	
			2.3 to 2.7	1.7	-	-	1.7	_	
			3.0 to 3.6	2.0	-	-	2.0	_	
V <sub>IL</sub>	Low-Level Input		0.9	-	GND	-	-	_	V
	Voltage		1.1 to 1.3	-	-	0.3 x V <sub>CC</sub>	-	0.3 x V <sub>CC</sub>	
			1.4 to 1.6	-	-	0.35 x V <sub>CC</sub>	-	0.35 x V <sub>CC</sub>	
			1.65 to 1.95	-	-	0.35 x V <sub>CC</sub>	-	0.35 x V <sub>CC</sub>	
			2.3 to 2.7	-	-	0.7	-	0.7	
			3.0 to 3.6	-	-	0.8	-	0.8	
V <sub>OH</sub>	High-Level Output	$V_{IN} = V_{IH}$ or $V_{IL}$							V
	Voltage	I <sub>OH</sub> = -20 μA	0.9	-	0.75	-	-	-	
		I <sub>OH</sub> = -0.3 mA	1.1 to 1.3	0.75 x V <sub>CC</sub>	-	-	0.75 x V <sub>CC</sub>	-	
		I <sub>OH</sub> = −1.7 mA	1.4 to 1.6	0.75 x V <sub>CC</sub>	-	-	0.75 x V <sub>CC</sub>	-	
		I <sub>OH</sub> = -3.0 mA	1.65 to 1.95	V <sub>CC</sub> - 0.45	-	-	V <sub>CC</sub> - 0.45	_	
		I <sub>OH</sub> = -4.0 mA	2.3 to 2.7	2.0	-	-	2.0	_	
		I <sub>OH</sub> = -8.0 mA	3.0 to 3.6	2.48	-	-	2.48	_	
V <sub>OL</sub>	Low-Level Output	$V_{IN} = V_{IH}$ or $V_{IL}$							V
	Voltage	I <sub>OL</sub> = 20 μA	0.9	-	0.1	-	-	-	
		I <sub>OL</sub> = 0.3 mA	1.1 to 1.3	=	-	0.25 x V <sub>CC</sub>	=	0.25 x V <sub>CC</sub>	
		I <sub>OL</sub> = 1.7 mA	1.4 to 1.6	=	-	0.25 x V <sub>CC</sub>	=	0.25 x V <sub>CC</sub>	
		I <sub>OL</sub> = 3.0 mA	1.65 to 1.95	=	-	0.45	=	0.45	
		I <sub>OL</sub> = 4.0 mA	2.3 to 2.7	=	-	0.4	=	0.4	
		I <sub>OL</sub> = 8.0 mA	2.7 to 3.6	=	-	0.4	=	0.4	
I <sub>IN</sub>	Input Leakage Current	V <sub>IN</sub> = 0 V to 3.6 V	0.9 to 3.6	-	-	±0.1	-	±1.0	μА
I <sub>OFF</sub>	Power Off Leakage Current	V <sub>IN</sub> = 0 V to 3.6 V; V <sub>OUT</sub> = 0 V to 3.6 V	0	-	-	1.0	-	10.0	μΑ
I <sub>CC</sub>	Quiescent Supply Current	V <sub>IN</sub> = V <sub>CC</sub> or GND	0.9 to 3.6	-	-	1.0	-	10.0	μΑ
I <sub>OZ</sub>	3-State Output Leakage Current	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> V <sub>OUT</sub> = 0 to 3.6V	0.9 to 3.6	-	-	1.0	-	10.0	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

**Table 4. AC ELECTRICAL CHARACTERISTICS** 

					T <sub>A</sub> = 25 °C		T <sub>A</sub> -55°C to	= +125°C	
Symbol	Parameter	Test Condition	V <sub>CC</sub> (V)	Min	Тур	Max	Min	Max	Unit
t <sub>PLH</sub> ,	Propagation Delay,	C <sub>L</sub> = 10 pF,	0.9	-	44.4	-	-	-	ns
t <sub>PHL</sub>	A to Y	$R_L = 1 M\Omega$	1.1 to 1.3	-	10.8	29.2	-	33.9	
			1.4 to 1.6	-	5.0	8.5	-	10.0	
			1.65 to 1.95	-	4.0	6.2	-	6.7	
			2.3 to 2.7	-	2.6	3.9	-	4.4	
			3.0 to 3.6	-	2.1	3.1	-	3.7	
		C <sub>L</sub> = 15 pF,	0.9	-	44.9	_	-	-	ns
		$R_L = 1 M\Omega$	1.1 to 1.3	-	11.0	29.9	-	34.7	
			1.4 to 1.6	-	5.6	9.3	-	11.2	
			1.65 to 1.95	-	4.5	6.9	-	7.1	
			2.3 to 2.7	-	2.9	4.4	-	5.0	
			3.0 to 3.6	-	2.4	3.4	-	3.9	
		C <sub>L</sub> = 30 pF,	0.9	-	46.2	_	-	-	ns
		$R_L = 1 M\Omega$	1.1 to 1.3	-	11.6	32.0	-	37.1	
			1.4 to 1.6	-	8.2	13.1	-	15.9	
			1.65 to 1.95	-	6	9.2	-	9.6	
			2.3 to 2.7	-	4	5.7	-	6.1	
			3.0 to 3.6	-	3.3	4.4	-	4.8	
t <sub>PZH</sub> ,	Output Enable Time,	C <sub>L</sub> = 10 pF;							ns
$t_{PZL}$	OE to Y	$R_L$ = 100 $k\Omega$	0.9	-	43.3	_	-	-	
		$R_L = 5 \text{ k}\Omega$	1.1 to 1.3	-	10.5	29.0	-	33.7	
		$R_L = 5 \text{ k}\Omega$	1.4 to 1.6	-	5.3	7.8	-	8.3	
		$R_L = 5 \text{ k}\Omega$	1.65 to 1.95	-	3.9	5.5	-	5.9	
		$R_L = 5 \text{ k}\Omega$	2.3 to 2.7	-	2.5	3.5	-	3.8	
		$R_L = 5 \text{ k}\Omega$	3.0 to 3.6	-	2.1	2.7	-	3	
		C <sub>L</sub> = 15 pF;							ns
		$R_L$ = 100 k $\Omega$	0.9	-	43.8	_	-	-	
		$R_L = 5 \text{ k}\Omega$	1.1 to 1.3	-	10.7	29.7	-	34.5	
		$R_L = 5 \text{ k}\Omega$	1.4 to 1.6	-	5.9	8.9	-	11	
		$R_L = 5 \text{ k}\Omega$	1.65 to 1.95	-	4.4	6.3	-	6.5	
		$R_L = 5 \text{ k}\Omega$	2.3 to 2.7	-	2.9	3.9	-	4.2	
		$R_L = 5 \text{ k}\Omega$	3.0 to 3.6	-	2.3	3	-	3.3	
		C <sub>L</sub> = 30 pF;							ns
		$R_L$ = 100 k $\Omega$	0.9	-	45.1	-	-	-	1
		$R_L = 5 \text{ k}\Omega$	1.1 to 1.3	-	11.2	31.8	-	36.9	1
		$R_L = 5 \text{ k}\Omega$	1.4 to 1.6	-	8.3	12.2	-	13.7	1
		$R_L = 5 \text{ k}\Omega$	1.65 to 1.95	-	6.1	8.6	-	9.7	1
		$R_L = 5 \text{ k}\Omega$	2.3 to 2.7	-	3.8	5	-	5.5	1
		$R_L = 5 \text{ k}\Omega$	3.0 to 3.6	-	2.9	3.8	-	4.2	1

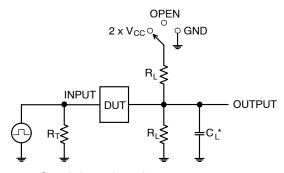
**Table 4. AC ELECTRICAL CHARACTERISTICS** 

					T <sub>A</sub> = 25 °(		T⊿ -55°C to	∆ = D +125°C	
Symbol	Parameter	Test Condition	V <sub>CC</sub> (V)	Min	Тур	Max	Min	Max	Unit
t <sub>PHZ</sub> ,	Output Disable Time, <del>OE</del> to Y	C <sub>L</sub> = 10 pF;							ns
$t_{PLZ}$	OE 10 Y	$R_L = 100 \text{ k}\Omega$	0.9	-	89.6	-	-	-	
		$R_L = 5 \text{ k}\Omega$	1.1 to 1.3	-	9.1	16.5	-	22.4	
		$R_L = 5 \text{ k}\Omega$	1.4 to 1.6	-	7.1	9.1	-	10.4	
		$R_L = 5 \text{ k}\Omega$	1.65 to 1.95	-	6.5	8.3	-	9	
		$R_L = 5 \text{ k}\Omega$	2.3 to 2.7	-	5.8	7.3	-	8.8	
		$R_L = 5 \text{ k}\Omega$	3.0 to 3.6	-	5.4	10.1	-	10.3	
		C <sub>L</sub> = 15 pF;							ns
		$R_L$ = 100 k $\Omega$	0.9	-	117.8	-	-	-	
		$R_L = 5 \text{ k}\Omega$	1.1 to 1.3	-	9.8	18.4	-	25.1	
		$R_L = 5 \text{ k}\Omega$	1.4 to 1.6	-	7.8	9.8	-	11.3	
		$R_L = 5 \text{ k}\Omega$	1.65 to 1.95	-	7.2	9.2	-	10.6	
		$R_L = 5 \text{ k}\Omega$	2.3 to 2.7	-	7	8.2	-	10.3	
		$R_L = 5 \text{ k}\Omega$	3.0 to 3.6	-	6.6	11.1	-	11.3	
		C <sub>L</sub> = 30 pF;							ns
		$R_L = 100 \text{ k}\Omega$	0.9	-	202.1	-	-	-	
		$R_L = 5 \text{ k}\Omega$	1.1 to 1.3	-	13.2	24.3	-	31.9	
		$R_L = 5 \text{ k}\Omega$	1.4 to 1.6	-	12.2	13.5	-	14.9	
		$R_L = 5 \text{ k}\Omega$	1.65 to 1.95	-	11.4	12.7	-	13.9	
		$R_L = 5 \text{ k}\Omega$	2.3 to 2.7	-	11.3	12.2	-	13.5	
		$R_L = 5 \text{ k}\Omega$	3.0 to 3.6	-	10.2	14.8	-	15.1	
C <sub>IN</sub>	Input Capacitance		0 to 3.6		3	-	-	-	pF
Co	Output Capacitance	V <sub>O</sub> = GND	0		3	-	-	-	pF
$C_{PD}$	Power Dissipation Capacitance (Note 5)	f = 10 MHz	0.9 to 3.6	-	4	-	-	-	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product

performance may not be indicated by the Electrical Characteristics for the listed test conditions.

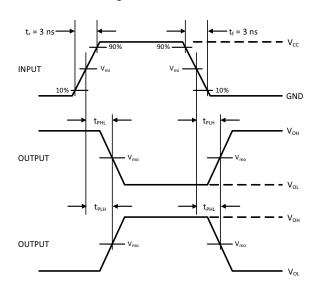
5. C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>. C<sub>PD</sub> is used to determine the no-load dynamic power consumption; P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.



Test	Switch Position
t <sub>PLH</sub> / t <sub>PHL</sub>	Open
t <sub>PLZ</sub> / t <sub>PZL</sub>	2 x V <sub>CC</sub>
t <sub>PHZ</sub> / t <sub>PZH</sub>	GND

 $C_L$  includes probe and jig capacitance  $R_T$  is  $Z_{OUT}$  of pulse generator (typically 50 W)  $f=1\ MHz$ 

Figure 5. Test Circuit



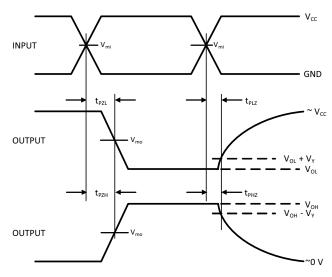


Figure 6. Switching Waveforms

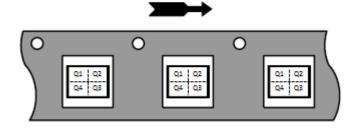
V <sub>CC</sub> , V	V <sub>mi</sub> , V	$V_{mo}$ , $V$	V <sub>Y</sub> , V
0.9	V <sub>CC</sub> /2	V <sub>CC</sub> /2	0.1
1.1 to 1.3	V <sub>CC</sub> /2	V <sub>CC</sub> /2	0.1
1.4 to 1.6	V <sub>CC</sub> /2	V <sub>CC</sub> /2	0.1
1.65 to 1.95	V <sub>CC</sub> /2	V <sub>CC</sub> /2	0.15
2.3 to 2.7	V <sub>CC</sub> /2	V <sub>CC</sub> /2	0.15
3.0 to 3.6	1.5	1.5	0.3

#### **ORDERING INFORMATION**

Device	Marking	Pin 1 Orientation (See below)	Package	Shipping <sup>†</sup>
NL17SG125DFT2G	A4	Q4	SC-88A	3000 / Tape & Reel
NL17SG125P5T5G	F (Rotated 90°CW)	Q2	SOT-953	8000 / Tape & Reel
NL17SG125MU1TCG (Contact <b>onsemi</b> )	TBD	Q4	UDFN6 1.45 x 1 mm	3000 / Tape & Reel
NL17SG125MU3TCG (Contact <b>onsemi</b> )	TBD	Q4	UDFN6 1 x 1 mm	3000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# PIN 1 ORIENTATION IN TAPE AND REEL Direction of Feed

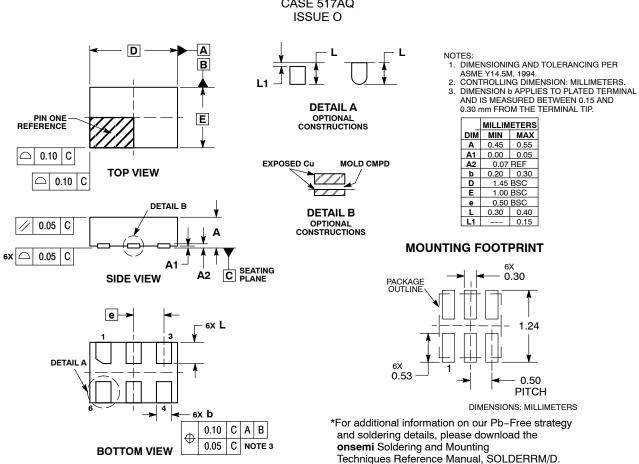


MiniGate is trademark of Semiconductor Components Industries, LLC (SCILLC) or its subsidiaries in the United States and/or other countries.

<sup>\*-</sup>Q Suffix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

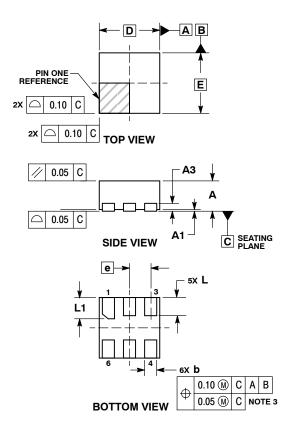
#### **PACKAGE DIMENSIONS**

# UDFN6, 1.45x1.0, 0.5P CASE 517AQ



#### **PACKAGE DIMENSIONS**

UDFN6, 1x1, 0.35P CASE 517BX ISSUE O



- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

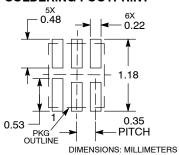
  2. CONTROLLING DIMENSION: MILLIMETERS.

  3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP.

  4. PACKAGE DIMENSIONS EXCLUSIVE OF BURRS AND MOLD FLASH.

	MILLIMETERS				
DIM	MIN	MAX			
Α	0.45	0.55			
A1	0.00	0.05			
А3	0.13	REF			
q	0.12	0.22			
D	1.00	BSC			
Е	1.00	BSC			
е	0.35 BSC				
L	0.25	0.35			
L1	0.30	0.40			

# RECOMMENDED SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting
Techniques Reference Manual, SOLDERRM/D.



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#### SC-88A (SC-70-5/SOT-353) CASE 419A-02 ISSUE M

**DATE 11 APR 2023** 

#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETERS
- DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.1016MM PER SIDE.

	МТ	RS		
DIM				
	MIN.	N□M.	MAX.	
А	0.80	0.95	1.10	
A1			0.10	
A3	0.20 REF			
b	0.10	0.20	0.30	
С	0.10		0.25	
D	1.80	2.00	2,20	
Е	2.00	2.10	2,20	
E1	1.15	1.25	1.35	
е	0.65 BSC			
L	0.10 0.15 0.30			

- 419A-01 DBSDLETE, NEW STANDARD 419A-02

	A3
40	0.50

5X b

◆ 0.2 M B M

#### RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

5. COLLECTOR

## **GENERIC MARKING DIAGRAM\***



\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

XXX = Specific Device Code

= Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE 1	PIN 1. SOURCE 1	PIN 1. CATHODE
2. EMITTER	<ol><li>EMITTER</li></ol>	2. N/C	2. DRAIN 1/2	2. COMMON ANODE
3. BASE	3. BASE	3. ANODE 2	<ol><li>SOURCE 1</li></ol>	3. CATHODE 2
4. COLLECTOR	<ol><li>COLLECTOR</li></ol>	<ol><li>CATHODE 2</li></ol>	4. GATE 1	4. CATHODE 3
<ol><li>COLLECTOR</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>CATHODE 1</li></ol>	5. GATE 2	<ol><li>CATHODE 4</li></ol>
0T) (1 F 0:	OT) (1 F. 7:	OT)// F 0:	STYLE 9:	Note: Disease refer to detect and for
STYLE 6:	STYLE 7:	STYLE 8:		Note: Please refer to datasheet for
PIN 1. EMITTER 2	PIN 1. BASE	PIN 1. CATHODE	PIN 1. ANODE	style callout. If style type is not called
2. BASE 2	<ol><li>EMITTER</li></ol>	2. COLLECTOR	2. CATHODE	, , ,
3. EMITTER 1	3. BASE	3. N/C	3. ANODE	out in the datasheet refer to the device
4. COLLECTOR	<ol><li>COLLECTOR</li></ol>	4. BASE	4. ANODE	datachast ningut or nin assignment
<ol><li>COLLECTOR 2/BASE 1</li></ol>	<ol><li>COLLECTOR</li></ol>	5. EMITTER	5. ANODE	datasheet pinout or pin assignment.

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DESCRIPTION:	SC-88A (SC-70-5/SOT-35	3)	PAGE 1 OF 1	

5. EMITTER

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5. COLLECTOR 2/BASE 1

MILLIMFTERS

 $N\square M$ 

0.37

0.15

0.12

1.00

0.80

0.35 BSC

1.00

MIN

0.34

0.10

0.07

0.95

0.75

0.95





#### SOT-953 1.00x0.80x0.37, 0.35P CASE 527AE **ISSUE F**

**DATE 17 JAN 2024** 

MAX

0.40

0.20

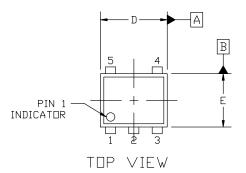
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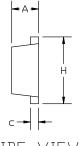
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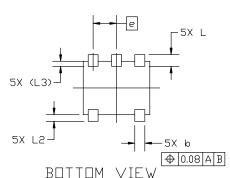
0.85

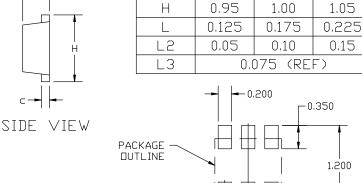
#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- CONTROLLING DIMENSION: MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.









0.350

DIM

Α

b

C

 $\mathbb{D}$ 

E

9 Н

# RECOMMENDED MOUNTING FOOTPRINT

\*For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

### **GENERIC MARKING DIAGRAM\***



= Specific Device Code

= Month Code

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DESCRIPTION:	SOT-953 1.00x0.80x0.37, 0	).35P	PAGE 1 OF 1

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